Abstracts

Current status and emerging trends in RF power FET technologies

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The growth in ISM and wireless communications markets, and the transition to 3G and embedded transceivers, are motivating an intense study of RFIC technologies. The power amplifier (PA) plays a critical role in the size, efficiency, and thermal requirements of wireless handsets. This paper reviews state-of-the-art and emerging power semiconductor devices for RF PAs. Comparisons are presented in terms of key specifications such as PAE, power gain, VSWR, package thermal resistance, and integrability.

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